

## Gradient influence on $P_{fi}$ of plane parallel electron chambers: Monte Carlo simulations and measurements.

Using EGS4 with an improved electron algorithm, the perturbation correction factor  $P_{repl}$  was calculated for the Markus chamber, the Roos chamber, and other, optimized chamber models and was compared to phantom measurements.  $P_{repl}$  is the product of the gradient correction factor  $P_{gr}$  and the fluence correction factor  $P_{fi}$ , caused by the differences in stopping power and scattering power, respectively. In this work the influence of the gradient on  $P_{fi}$  was investigated. It was found that  $P_{repl}(\text{Markus})$  drops from 0.99 to 0.90 for a mean electron energy at depth of 2 MeV when the chamber is moved upstream from  $d_{max}$  (0.75 cm,  $E_0 = 4$  MeV) to 0.186 mm ( $E_0 = 2.5$  MeV) due to  $P_{fi}$ .  $P_{repl}(\text{Roos})$  changes from 1 to 0.965 for the same case. For negative gradients, as in case of  $d_{max}$  measurements for low incident electron energies and for measurements beyond  $d_{max}$ ,  $P_{repl}$  raises above unity. The overall dependence of  $P_{repl}$  on the percentage change of depth between chamber entrance window and backwall is approximately linear with  $P_{repl} = 0.97 - 0.005 \text{ pdd}[\% \text{ mm}^{-1}]$  for the Markus chamber and  $P_{repl} = 1 - 0.001 \text{ pdd}[\% \text{ mm}^{-1}]$  for the Roos chamber for energies at depth below 3 MeV. Optimized chambers show a smaller dependence. Fricke dosimetry measurements using clinical electron beams were used to confirm the simulation results.